524,288 WORD × 8 BIT CMOS UV ERASABLE AND ELECTRICALLY PROGRAMMABLE READ ONLY MEMORY

DESCRIPTION

The TC544000P/F is a 524,288 word × 8 bit one time programmable read only memoly, and molded in a 32 pin plastic package. The access time of TC544000P/F is 120ns/150ns and has low power standby mode which reduces the power dissipation without increasing access time.

The electrical characteristics and programming method are the same as U.V. EPROM TC574000D's once programmed, the TC544000P/F can not be erased because of using plastic DIP without transparent window.

FEATURES

Peripheral circuit : CMOS

Memory cell : N-MOS

• Access time

	- 12	- 150
Vcc	5∨±5%	5V ± 10%
Temp	0°C~	70°C
tACC	120ns	150ns

-12 are satisfied with the specification of -150

• Low power dissipation

Active: 60mA/8.3MHz Standby: 100µA (Ta=70°C)

- · High speed programming operation
- Single 5V power supply
- Full static operation
- Input and output TTL compatible
- JEDEC standard 32 pin
- TC544000P : DIP32-P-600 TC544000F : SOP32-P-525

PIN CONNECTION (TOP VIEW)

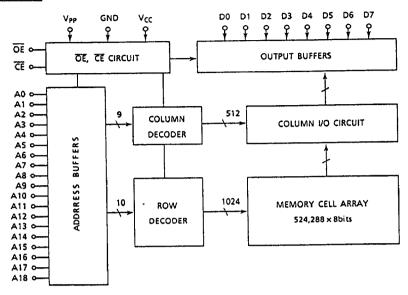
V _{PP} [1 32] V _{CC} A16 [2 31] A18 A15 [3 30] A17 A12 [4 29] A17 A17 [5 28] A13 A6 [6 27] A8 A5 [7 26] A9 A4 [8 25] A1 A3 [9 24] OE A2 [10 23] A10 A1 [11 22] CE A0 [12 21] D7 D0 [13 20] D6 D1 [14 19] D5 D2 [15 18] D4			
A12 [14 29] A14 A7 [15 28] A16 A6 [16 27] A8 A5 [7 26] A9 A4 [18 25] A11 A3 [19 24] D1 A1 [11 22] CE A0 [12 21] D7 D0 [13 20] D6 D1 [14 19] D5 D2 [15 18] D4	Vpp	d, ~	32) V _{cc}
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A0 [12 21] D7 D0 [13 20] D6 D1 [14 19] D5 D2 [15 18] D4	A1		22 T CE
D. 91	AO		21 07
D. 91		Ī13	20 D6
D. 91		D14	19 DS
		Ū15	18 D4
GND L116 17 L D3	GND	1 16	17 03
	7/7		

TC544000P/F

PIN NAMES

	· · · · · · · · · · · · · · · · · · ·	
A0~A18	Address Inputs	
D0~D7	Outputs (inputs)	
CE	Chip Enable Input	
ŌĒ	Output Enable Input	
Vcc	V _{CC} Supply Voltage	
Vpp	Program Supply Voltage	
GND	Ground	
	MMM. DataSh	eth J. com
51		

BLOCK DIAGRAM



MODE SELECTION

MODE	Œ	OE	Vpp	Vcc	D0~D7	Power	
Read	L	Ļ			Data Out	Active	
Output Deselect	•	н	5V	5∨	5∨	High Impedance	~~~
Standby	Н	•	1		High Impedance	Standby	
Program	L	н			Data In		
Program Inhibit	н	н	12.50V 6.25V		High Impedance	Active	
Program Verify		L			Data Out]	

^{* :} H or L

MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT
Vcc	V _{CC} Power Supply Voltage	-0.6~7.0	٧
Vpp	Program Supply Voltage	- 0.6~14.0	٧
ViN	Input Voltage	- 0.6~7.0	٧
V _{IN} (A9)	Input Voltage (A9)	-0.6~13.5	٧
Vvo	input/Output Voltage	- 0.6~V _{CC} + 0.5	٧
Po	Power Dissipation	1.5	w
TSOLDER	Soldering Temperature · Time	260 · 10	*C · sec
T _{strg}	Storage Temperature	- 65~125	•c
Topr	Operating Temperature	0~70	•c

READ OPERATION

DC RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	TC544000P/F-12	TC544000P/F-150
VIH	Input High Voltage	2.2V~V _{CC} +0.3V	2.2V~V _{CC} + 0.3V
ViL	Input Low Voltage	- 0.3V~0.8V	0.3V~0.8V
Vcc	V _{CC} Power Supply Voltage	5∨ ± 5%	5V ± 10%
Vpp	V _{PP} Power Supply Voltage	V _{CC} - 0.6V~V _{CC} + 0.6V	V _{CC} = 0.6V~V _{CC} + 0.6V

DC AND OPERATING CHARACTERISTICS (Ta=0~70°C)

SIMBOL	PARAMETER	TEST CONDITION		MIN.	TYP.	MAX.	UNIT	
lu	Input Current	V _{IN} = 0~V _{CC}		-	-	± 10	μА	
		CE = V _{IL}	f = 8.3MHz	-	-	60		
lcco1	Operating Current		1	f = 6.7MHz	<u> </u>	-	50	mA
Icco2			f=1MHz	_	-	15]	
Iccs 1		CE = V _{IH}		-	-	1	mA	
Iccsz	Standby Current	CE = V _{CC} - 0.	2∨	_	-	100	μΑ	
V _{OH}	Output High Voltage	I _{OH} = -400µ	ıA	2.4	-	-	V	
Vol	Output Low Voltage	I _{OL} = 2.1mA		_	-	0.4	V	
lpp1	V _{PP} Current	$V_{PP} = V_{CC} \pm 0.6V$		-	-	± 10	μΑ	
lo	Output Leakage Current	V _{OUT} = 0.4V~V _{CC}		-	-	± 10	μА	

AC CHARACTERISTICS ($Ta = 0 \sim 70^{\circ}C$, $V_{Pl'} = V_{CC} \pm 0.6V$)

5,1100	BARAMETER		TC544000P/F-12		TC544000P/F-150		TINU
SIMBOL	PARAMETER	TEST CONDITION	MIN.	MAX.	MIN.	MAX.	וואט
t _{ACC}	Address Access Time	CE = OE = VIL		120	_	150	ns
t _{CE}	CE to Output Valid	OE = VIL	_	120	-	150	ns
^t OE	OE to Output Valid	CE = V _{IL}	_	60	-	70	ns
t _{DF1}	CE to Output in High-Z	OE = VIL	0	50	0	60	ns
t _{DF2}	OE to Output in High-Z	CE = VIL	0	50	0	60	ns
t _{OH}	Output Data Hold Time	CE = OE = VIL	0	-	0	_	ns

TC544000P/F-12 are satisfied with the specification of TC544000P/F-150

AC TEST CONDITIONS

• Output Load : 1 TTL Gate and CL=100pF

Input Pulse Rise and Fall Times : 10ns Max.
 Input Pulse Levels : 0.45V~2.4V

• Timing Measurement Reference Level: Inputs 0.8V and 2.2V, Outputs 0.8V and 2.0V

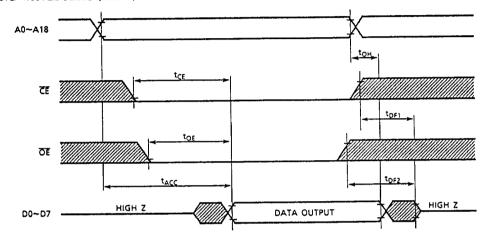


CAPACITANCE* (Ta=25°C, f=1MHz)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	MAX.	UNIT
CiN	Input Capacitance	V _{IN} = 0V	-	9	PF
Cout	Output Capacitance	V _{OUT} = 0V	-	13	1

^{*} This parameter is periodically sampled is not 100% tested.

TIMING WAVEFORMS (READ)



HIGH SPEED PROGRAM OPERATION

DC RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
ViH	Input High Voltage	2.2	-	V _{CC} + 1.0	٧
VIL	Input Low Voltage	- 0.3	-	0.8	٧
Vcc	V _{CC} Power Supply Voltage	6.00	6.25	6.50	٧
Vpp	V _{PP} Power Supply Voltage	12.20	12.50	12.80	٧

DC AND OPREATING CARACTERISTICS ($Ta=25\pm5^{\circ}C$, $V_{CC}=6.25V\pm0.25V$, $V_{PP}=12.50V\pm0.30V$)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
ILI	Input Current	V _{IN} = 0~V _{CC}	-		± 10	μΑ
V _{OH}	Output High Voltage	I _{OH} = - 400μA	2.4	1	_	V
Vol	Output Low Voltage	1 _{OL} = 2.1mA	-	ı	0.4	٧
lcc	V _{CC} Supply Current	-	•	*	30	mA
lpp2	V _{PP} Supply Current	V _{PP} = 12.8V	-	-	50	mA

AC PROGRAMMING CHARACTERISTICS (Ta=25 \pm 5°C, V_{CC}=6.25V \pm 0.25V, V_{PP}=12.50V \pm 0.30V)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
tas	Address Setup Time	-	2	•	-	μ\$
t _{AH}	Address Hold Time	-	2		_	μs
tCES	CE Setup Time	-	0	-	-	μs
t _{CEH}	CE Hold Time	-	o	-	-	μs
toes	ŌĒ Set up Time	-	2		-	μs
tos	Data Set up Time	-	2	_	-	μs
^t oн	Data Hold Time	-	2	-	-	μs
typs	V _{PP} Set up Time	-	2	-	-	μs
tvcs	V _{CC} Set up Time	-	2	-	-	μs
t _{PW}	Program Pulse Width	CE = V _{IL} , OE = V _{IH}	45	50	55	μs
^t OE	OE to Output Valid	Œ = V _{IH}	-	-	100	ns
t _{DFP}	OE to Output in High-Z	CE = VIH	-	-	90	ns

AC TEST CONDITIONS

• Output Load : 1 TTL Gate and CL (100pF)

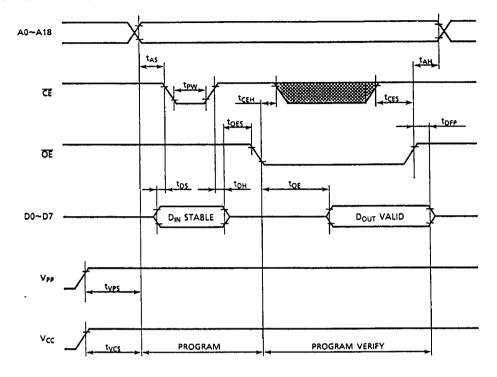
Input Pulse Rise and Fall Time : 10ns Max.
 Input Pulse Levels : 0.45V~2.4V

• Timing Measurement Reference Level: Input 0.8V and 2.2V, Output 0.8V and 2.0V



TIMING WAVEFORMS (PROGRAM)

HIGH SPEED PROGRAM OPERATION



Note 1. VCC must be applied simultaneously or before Vpp and cut off simultaneously or after Vpp.

- 2. Removing the device from socket and setting the device in socket with VPP=12.50V may cause permanent damage to the device.
- 3. The VPP supply voltage is permitted up to 14V for program operation. So the voltage over 14V should not be applied to the VPP terminal. When the switching pulse voltage is applied to the VPP terminal, the overshoot voltage of its pulse should not be exceeded 14V.

OPERATION INFORMATION

The TC544000P/F's six operation modes are listed in the following table. Mode selection can be achieved by applying TTL level signal to all inputs.

MODE	PIN NAMES (NUMBER)	CE (22)	OE (24)	V _{PP} (1)	V _{CC} (32)	D0~D7 (13~15, 17~21)	POWER	
Read Operation (Ta = 0~70°C)	Read	L	L			Data Out	Active	
	Output Deselet	•	н	5V	5∨	High Impedance		
	Standby	Н	*			High Impedance	Standby	
Program Operation (Ta = 25 ± 5°C)	Program	L	н	12.50V	6.25V	Data In	Active	
	Program Inhibit	Н	н			High Impedance		
	Program Verify	٠	L]		Data Out		

Note: H; VIH, L: VIL, *: VIH or VIL

READ MODE

The TC544000P/F has two control functions. The chip enable ($\overline{\text{CE}}$) controls the operation power and should be used for device selection. The output enable ($\overline{\text{OE}}$) controls the output buffers, independent of device selection. Assuming that $\overline{\text{CE}} = \overline{\text{OE}} = V_{\text{IL}}$, the output data is valid at the outputs after address access time from stabilizing of all addresses. The $\overline{\text{CE}}$ to output valid (tce) is equal to the address access time (tacc).

Assuming that $\overline{CE} = V_{IL}$ and all addresses are valid, the output data is valid at the outputs after top from the falling edge of \overline{OE} .

OUTPUT DESELECT MODE

Assuming that $\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$, the outputs will be in a high impedance state. So two or more TC544000P/F's can be connected together on a common bus line. When \overline{CE} is decoded for device selection, all deselected devices are in low power standby mode.

STANDBY MODE

The TC544000P/F has a low power standby mode controlled by the $\overline{\text{CE}}$ signal. By applying a high level to the $\overline{\text{CE}}$ input, the TC544000P/F is placed in the standby mode which reduce the operating current to 100µA by applying MOS-high level (V_{CC}) and then the outputs are in a high impedance state, independent of the $\overline{\text{OE}}$ inputs.



PROGRAM MODE

Initially, when received by customers, all bits of the TC544000P/F are in the "1" state which is erased state. Therefore the program operation is to introduce "0's" data into the desired bit locations by electrically programming. The TC544000P/F is in the programming mode when the Vpp input is at 12.50V and \overline{CE} is at Low under $\overline{OE} = V_{IH}$.

The TC544000P / F can be programmed any location at any time either individually, sequentially, or at random.

PROGRAM VERIFY MODE

The verigy mode is to check that desired data is correctly programmed on the programmed bits. The verify is accomplished with \overline{OE} at V_{IL} .

PROGRAM INHIBIT MODE

Under the condition that the program voltage (+12.50V) is applied to Vpp terminal, a high level $\overline{\text{CE}}$ and $\overline{\text{OE}}$ input inhibits the TC544000P/F from being programmed.

Programming of two or more TC544000P / F's in parallel with different data is easily accomplished. That is, all inputs except for \overline{CE} and \overline{OE} may be commonly connected, and a low level program pulse is applied to the \overline{CE} of the desired device only and high level signal is applied to the other devices.

HIGH SPEED PROGRAM MODE

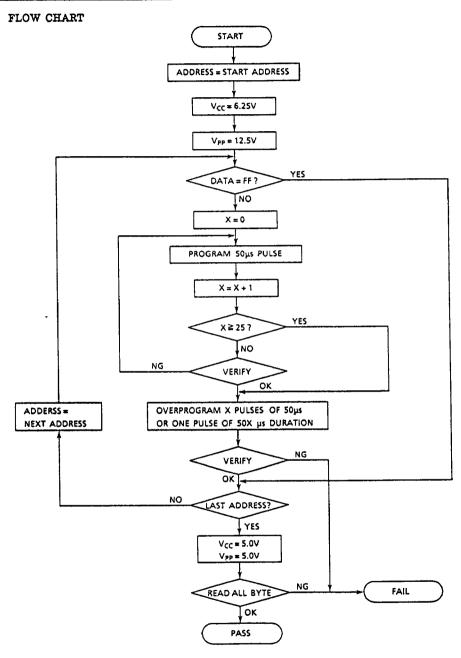
The device is set up is the high speed programming mode when the programming voltage (+12.50V) is applied to the Vpp terminal with Vcc=6.25V.

The programming is achieved by applying a single low level 50µs pulse to the $\overline{\text{CE}}$ input after addresses and data are stable. Then the programmed data is verified by using Program Verify Mode. If the programmed data is not correct, another program pulse of 50µs is applied and then the programmed data is verified. This should be repeated until the program operates correctly (max. 25 times).

After correctly programming the selected address, the additional program pulse with width of 1 time more than that needed for initial programming is applied.

When programming has been completed, the data in all addresses should be verified with $V_{CC} = V_{PP} = 5V$.

HIGH SPEED PROGRAM MODE





ELECTRIC SIGNATURE MODE

Electric signature mode allows to read out a code from TC544000P/F which identifies its manufacturer and device type.

The programming equipment may reads out manufacturer code and device code from TC544000P/F by using this mode before program operation and automatically set program voltage (Vpp) and algorithm.

Electric Signature mode is set up when 12V is applied to address line A9 and the rest of address lines is set to V_{IL} in read operation. Data output in this conditions is manufacturer code. Device code is identified when address A0 is set to V_{IH}.

These two codes possess an odd parity with the parity bit of MSB (D7).

The following table shows electric signature of TC544000P/F.

SIGNATURE	Α0	D7	Dε	D5	D4	D3	D2	D1	DO	HEX. DATA
Manufacture Code	ViL	1	0	0	1	1	0	0	0	98
Device Code	V _{IH}	1	0	0	0	1	1	0	0	8C

Notes: A9=12V±0.5V

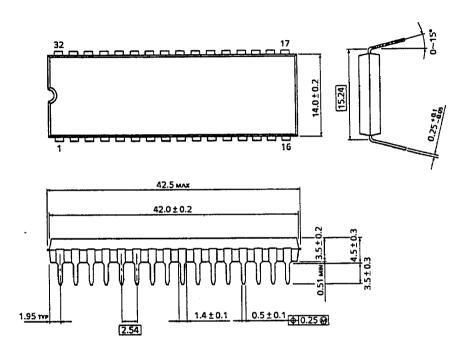
A1~A8, A10~A18, \overline{CE} , $\overline{OE} = V_{IL}$

OUTLINE DRAWINGS

• Plastic DIP

DIP32-P-600

Unit: mm



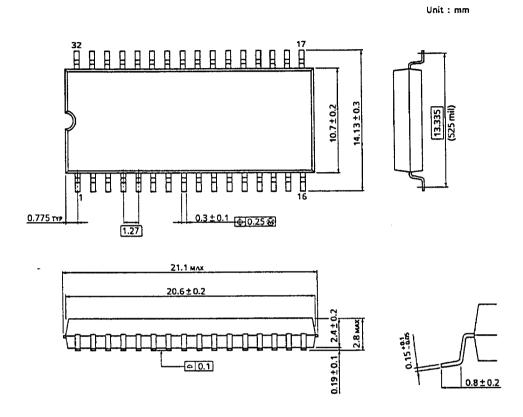
Weight: 4.25g (TYP.)

Note: Package width and length do not include mold protrusion, allowable mode protrusion is 0.15mm.

OUTLINE DRAWINGS

• Plastic SOP

SOP32-P-525



Weight: 1.10g (TYP.)

Note: Package width and length do not include mold protrusion, allowable mode protrusion is 0.15mm.